



THE DATASHEET OF ZVN2120A



Obsolete. A

**N-CHANNEL ENHANCEMENT
MODE VERTICAL DMOS FET**

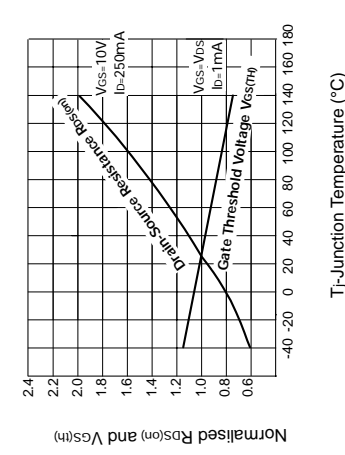
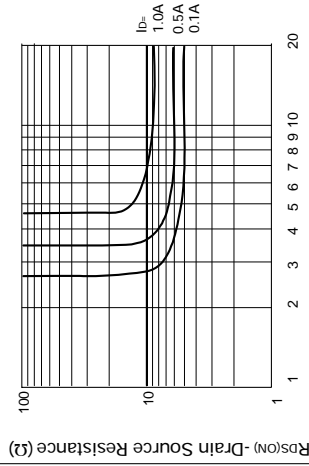
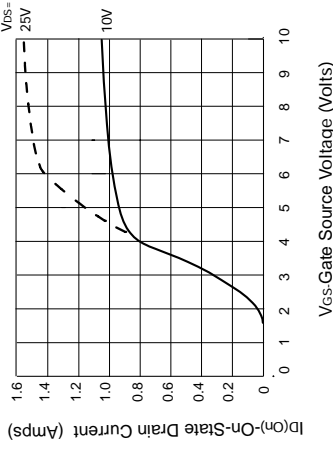
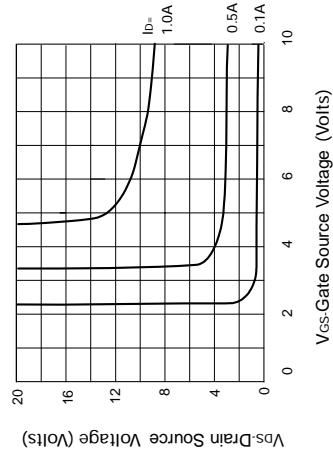
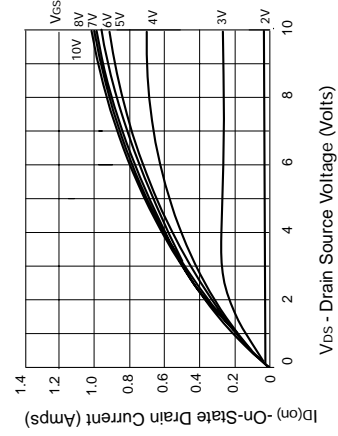
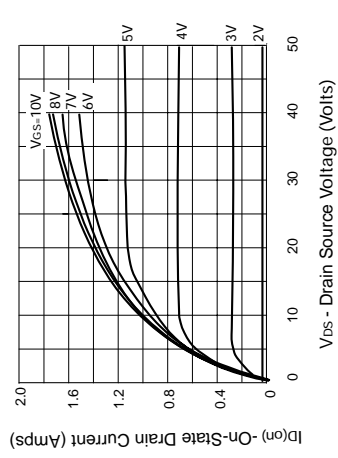
ISSUE 2 – MARCH 94

FEATURES

- * 200 Volt V_{DS}
- * $R_{DS(on)} = 10\Omega$

ZVN2120A

TYPICAL CHARACTERISTICS



ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current (1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{riss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

(1) Measured under pulsed conditions. With $V_{GS} = 10V$, $I_D = 10mA$, $V_{DS} = 10V$, $t_{rise} = 10ns$, $t_{fall} = 10ns$, $f = 10kHz$.
 (2) Sample test.

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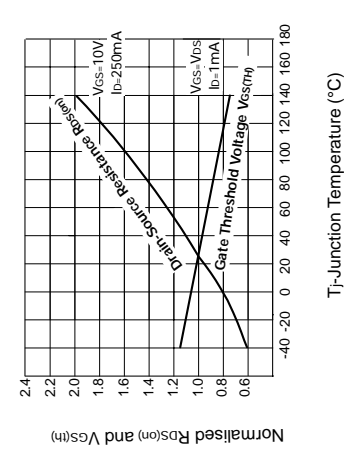
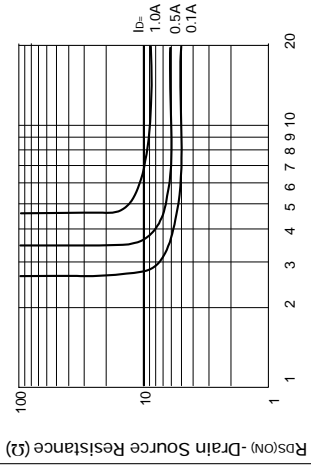
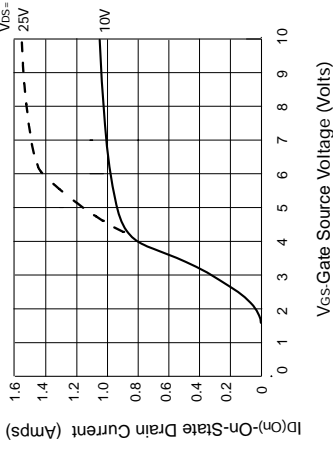
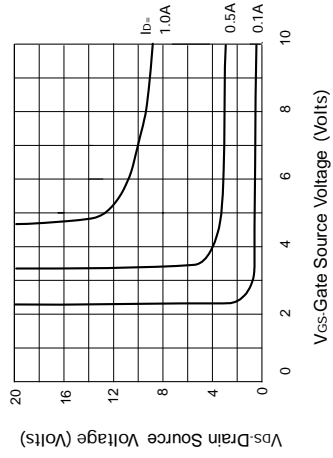
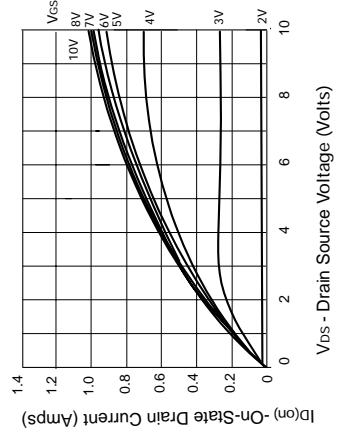
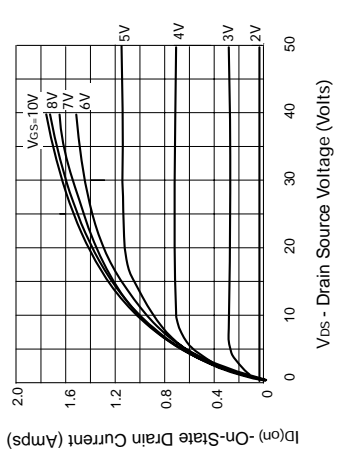
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FEATURES

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TYPICAL CHARACTERISTICS



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL
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Pulsed Drain Current	I_{GSS}
Gate Source Voltage	I_{DSS}
Power Dissipation at $T_{amb}=25^{\circ}C$	$I_{D(on)}$
Operating and Storage Temperature Range	$R_{DS(on)}$

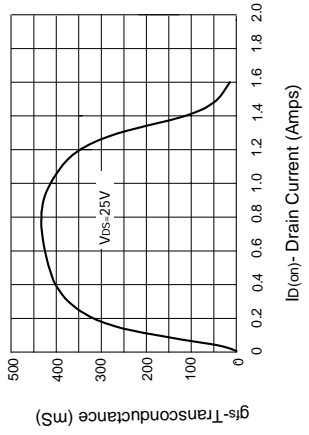
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Fall Time (2)(3)	t_f

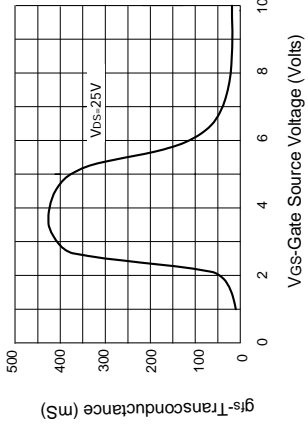
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- (2) Sample test.

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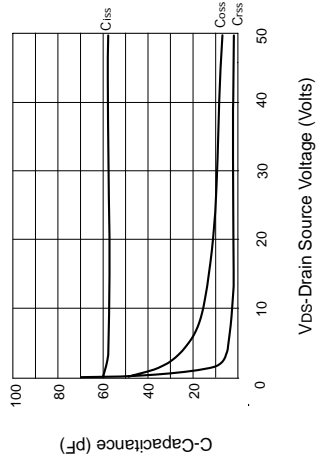
TYPICAL CHARACTERISTICS



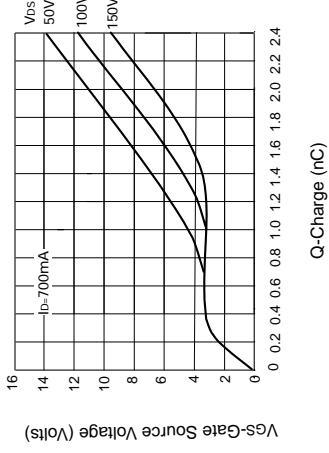
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

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